

Title (en)

CIRCUIT ARRANGEMENT FOR CREATING A MOS CAPACITOR WITH A LOWER VOLTAGE DEPENDENCY AND A LOWER SURFACE AREA REQUIREMENT

Title (de)

SCHALTUNGSANORDNUNG ZUR BILDUNG EINES MOS-KONDENSATORS MIT GERINGER SPANNUNGSABHÄNGIGKEIT UND GERINGEM FLÄCHENBEDARF

Title (fr)

ENSEMBLE CIRCUIT SERVANT A FORMER UN CONDENSATEUR MOS A FAIBLE DEPENDANCE VIS-A-VIS DE LA TENSION ET A FAIBLE ENCOMBREMENT

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Application

EP 00978967 A 20000929

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Abstract (en)

[origin: WO0124277A1] The invention relates to a circuit arrangement, comprising short-channel MOS transistors (T1, T2) of the same channel type which are not connected in series or parallel and in particular, to their exclusive depletion mode in the required voltage area. The circuit arrangement achieves a considerable increase in the effective capacitance (A, B) in relation to circuit arrangements comprising conventional long channel MOS transistors, by the use of extrinsic capacitances. Said circuits reduce both the surface area requirement and costs.

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